

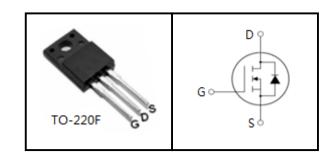
650V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information				
Device Package		Marking		
CS16N65F	TO-220F	CS16N65F		

Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted							
Parameter	Symbol	Value	Unit				
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	650	V				
Continuous Drain Current	I _D	16	А				
Pulsed Drain Current (note1)	I _{DM}	64	А				
Gate-Source Voltage	V _{GSS}	±30	V				
Single Pulse Avalanche Energy (note2)	E _{AS}	460	mJ				
Avalanche Current (note1)	I _{AS}	9.6	А				
Repetitive Avalanche Energy (note1)	E _{AR}	276	mJ				
Power Dissipation (T _C = 25°C)	P _D	98	W				
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C				

Thermal Resistance				
Parameter	Symbol	Value	Unit	
Thermal Resistance, Junction-to-Case	R_{thJC}	1.27	14004	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	K/W	



Specifications $T_J = 25^{\circ}C$, unless otherwise noted								
Davamatar	0	Total October 1985 and	Value			11.24		
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650			V		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA		
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30V$			±100	nA		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		4.0	V		
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 8A		0.45	0.55	Ω		
Dynamic								
Input Capacitance	C _{iss}	$V_{GS} = 0V$,		2063		pF		
Output Capacitance	C _{oss}	$V_{DS} = 25V$,		204				
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		29				
Total Gate Charge	Q_g			74		nC		
Gate-Source Charge	Q_{gs}	$V_{DD} = 520V, I_{D} = 16A,$ $V_{GS} = 10V$		10				
Gate-Drain Charge	Q_gd	55		40				
Turn-on Delay Time	t _{d(on)}			54		ns		
Turn-on Rise Time	t _r	$V_{DD} = 325V, I_{D} = 16A,$		40				
Turn-off Delay Time	t _{d(off)}	$R_G = 25 \Omega$		312				
Turn-off Fall Time	t _f			66				
Drain-Source Body Diode Character	istics							
Continuous Body Diode Current	Is	T 25.0C			16	A		
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			64			
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}\text{C}, I_{SD} = 8\text{A}, V_{GS} = 0\text{V}$			1.4	٧		
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V, I_{S} = 16A,$		682		ns		
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /µs		4.5		μC		

2

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}C$
- 3. Pulse Test: Pulse width \leq 300 μ s, Duty Cycle \leq 1%



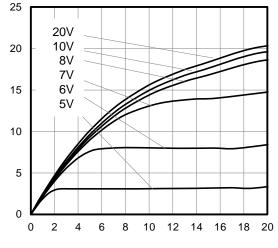
I_D, Drain Current (A)

ID, Drain Current (A)

I_D, Drain Current (A)

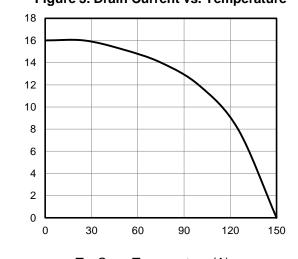
Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted





V_{DS}, Drain-to-Source Voltage (V)

Figure 3. Drain Current vs. Temperature



T_C, Case Temperature (A)

Figure 5. Transfer Characteristics

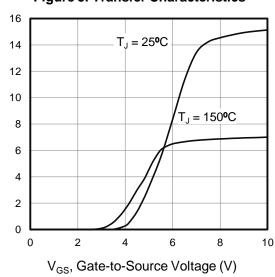
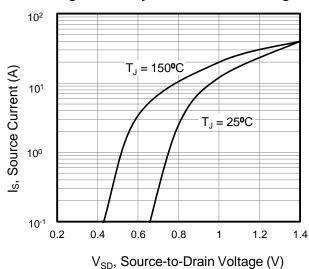
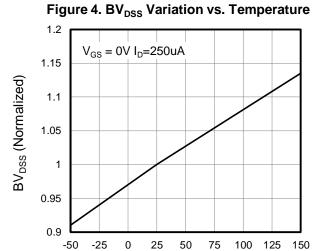


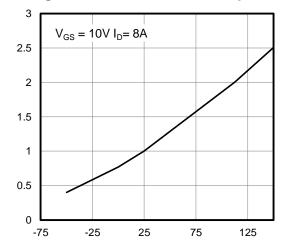
Figure 2. Body Diode Forward Voltage





T_C, Case Temperature (°C)

Figure 6. On-Resistance vs. Temperature



T_J, Junction Temperature (°C)

RDS(on), On-Resistance (Normalized)



Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

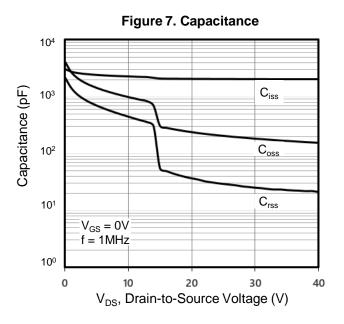


Figure 8. Gate Charge

10

V_{DD} = 130V

V_{DD} = 325V

V_{DD} = 520V

V_{DD} = 520V

0

0 5 10 15 20 25 30 35 40 45 50 55 60 65 70 75

Q_g, Total Gate Charge (nC)

Figure 9. Transient Thermal Impedance

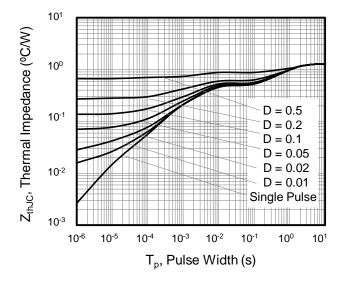




Figure A: Gate Charge Test Circuit and Waveform

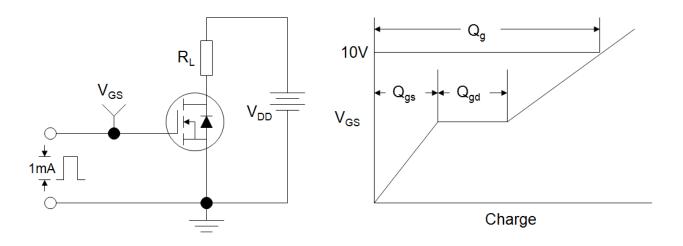


Figure B: Resistive Switching Test Circuit and Waveform

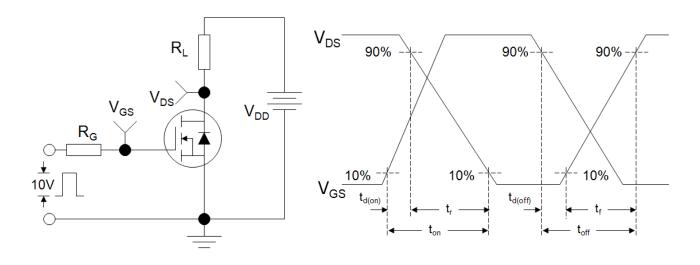
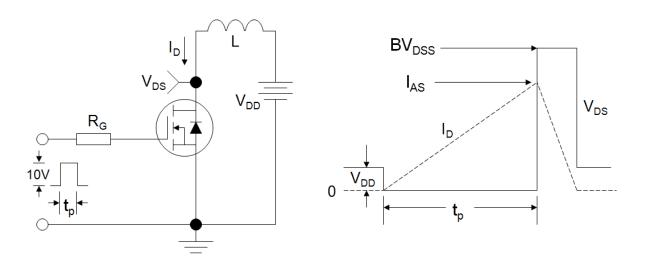
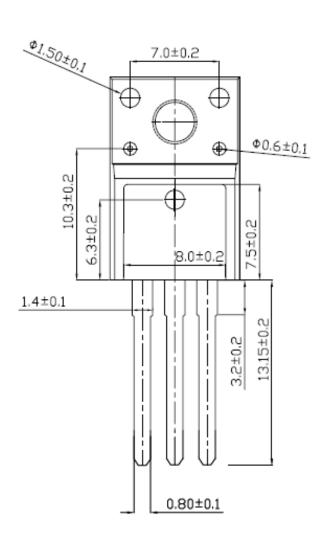


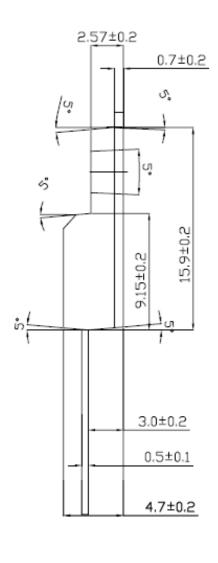
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-220F







Disclaimer

All product specifications and data are subject to change without notice.

For documents and material available from this datasheet, Suzhou Convert does not warrant or assume any legal liability or responsibility for the accuracy, completeness of any product or technology disclosed hereunder.

No license, express or implied, by estoppels or otherwise, to any intellectual property rights is granted by this document or by any conduct of Suzhou Convert.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless. Customers using or selling Suzhou Convert products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Suzhou Convert for any damages arising or resulting from such use or sale.

Suzhou Convert disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Suzhou Convert's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

Suzhou Convert SemiConductor CO., Ltd. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

In the event that any or all Suzhou Convert products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Suzhou Convert believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.